High quality ultraviolet AlGaN/GaN multiple quantum wells with atomic layer deposition grown AlGaN barriers

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Low dislocation density ultraviolet (UV) AlGaN/GaN multiple quantum well (MQW) structure was grown using atomic layer deposition (ALD) technique. The AlGaN/GaN MQW grown on the sapphire substrate consisted of three GaN QWs and four AlGaN barriers formed by ALD grown AlN/GaN superlattices. The as-grown sample showed smooth surface morphology with a root-mean-square roughness value of only 0.35 nm, and no surface cracks were found. The dislocation density was estimated to be as low as $3.3 \times 10^7 \text{cm}^{-2}$. X-ray and transmission electron microscope data showed the MQW had sharp interfaces with good periodicity. The sample had an UV photoluminescence emission at 334 nm (3.71 eV) with a very narrow linewidth of 47 meV at 13 K. The cathodoluminescence image revealed a fairly uniform luminescence pattern at room temperature. The AlGaN/GaN MQW grown by ALD technique should be useful for providing high crystalline quality for fabrication of various optical devices. © 2008 American Institute of Physics.

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The AlGaN/GaN multiple quantum wells (MQWs) have attracted much attention because of their unique properties, such as a high conduction band offset, better carrier confinement, large longitudinal (LO) phonon energy, and ultrafast carrier and intersubband relaxation, making AlGaN/GaN MQWs promising structures for realizing ultraviolet light emitting diodes and laser diodes. Recent reports indicated that the optical and electrical properties of AlGaN/GaN MQWs were very sensitive to the crystalline quality and the threading dislocation density in the AlGaN/GaN epilayer. So far most AlGaN/GaN MQWs structures were grown on lattice-mismatched foreign substrates such as sapphire, making it difficult to grow device-quality MQWs due to the lattice mismatch and the misfit in the thermal expansion coefficients between these two material systems. Recently high quality AlGaN/GaN heterostructures using quasi-AlGaN formed by AlN/GaN superlattices (SLs) as barrier layers were reported. However, these results mainly focused on the electrical properties used for AlGaN/GaN high electron mobility transistors and no optical properties were reported. In this paper, we report the growth of low dislocation density and crack-free AlGaN/GaN MQWs by using the atomic layer deposition (ALD) grown AlN/GaN SLs as the AlGaN barrier. The as-grown AlGaN/GaN MQWs sample had low defect density, smooth surface morphology with small root-mean-square (rms) roughness value and sharp interfaces. In addition, the AlGaN/GaN MQWs sample showed a sharp photoluminescence (PL) spectrum and a uniform cathodoluminescence (CL) pattern.

The AlGaN/GaN MQW structures were grown by the low-pressure metal-organic chemical vapor deposition VEECO D75 system. The trimethylgallium (TMGa), trimethylaluminium (TMAI), and gaseous NH$_3$ were employed as the reactant sources for Ga, Al, and N, respectively, and H$_2$ and N$_2$ were used as the carrier gaseous. The (0001)-oriented sapphire substrate with a 0.2° offset was first heated to 1000 °C under a H$_2$ ambient for 5 min. Then, a 2-μm-thick GaN epilayer was grown after the deposition of a low-temperature nucleation layer. Finally, the AlGaN/GaN MQWs structure comprising three GaN wells and four AlGaN barriers were grown at 850 °C in H$_2$ + N$_2$ atmosphere. Particularly, the AlGaN barriers were grown using the ALD technique. The ALD process involves alternate control of mass flow of TMAI and TMGa gases during the growth of AlGaN barrier to form six pairs of AlN/GaN SLs. Figure 1 shows the growth procedure of the AlGaN barrier and GaN well layer. The TMAI and TMGa flow times of AlN and GaN layers were 6.8 and 19.8 s, respectively, under a continuous flow of the NH$_3$ gas at 850 °C. The growth rate of the ALD grown AlGaN barrier measured by an in situ Filmetrics optical monitoring system was about 0.14 μm/h. After the AlGaN barrier was grown, only TMGa was introduced into the reactor for 34.8 s to grow the GaN well.

![FIG. 1. (Color online) Growth procedure of AlGaN barrier and GaN well layers.](image-url)
The surface morphology of the as-grown sample was observed by atomic force microscope (AFM) with a scanning area of $5 \times 5$ μm$^2$. A high resolution x-ray diffraction (HRXRD) and reciprocal space mapping (RSM) were performed using Cu $K\alpha$ radiation. The average thicknesses of the AlGaN barriers and the GaN wells were determined from the angular distribution of the x-ray source. The average thicknesses of AlGaN barriers and GaN wells can be fitted to be about 0.42, 0.77, and 2.9 nm, respectively. The average Al content of AlGaN barrier is also estimated to be about 3.2 at%.

Figures 2(a) and 2(b) show the HRXRD $\omega/2\theta$ diffraction pattern and the RSM of the as-grown AlGaN/GaN MQWs sample. In Fig. 2(a), the HRXRD diffraction pattern shows two periodical structures: one can be attributed to the AlGaN/GaN MQWs; another can be attributed to the AlN/GaN SLs in the AlGaN barriers. The third order satellite peak of the diffraction pattern for AlGaN/GaN MQWs can be clearly observed, suggesting the high crystalline quality of AlGaN/GaN MQWs and AlN/GaN SLs. The average Al content of AlGaN in the barrier and the GaN wells can be fitted to be about 0.42, 0.77, and 2.9 nm, respectively. The average Al content of AlGaN barrier is also estimated to be about 3.2 at%.

Fig. 3(a) shows the plane-view bright-field TEM image from the AlGaN/GaN MQWs region is only 2.5 $\times$ 10$^{-6}$, indicating that the AlGaN epilayer is fully strained and pseudomorphic to the underlying GaN layer.

As shown in Fig. 3(a), the surface morphology of the top layer was observed by AFM and no cracks were found. A very small rms value of the surface roughness of 0.35 nm was achieved. To carefully investigate the threading dislocation within our sample, both cross-sectional and plane-view TEM images were taken. Figure 3(b) shows the cross-sectional TEM image of the sample with the white dash lines indicating the top and bottom GaN epilayer regions. It is clear that few dislocations are observable and only one dislocation passes through the GaN epilayer into AlGaN/GaN MQWs. The dislocation density (DD) at the bottom GaN layer is about 3.5 $\times$ 10$^{10}$ cm$^{-2}$ and slightly reduces to 1.4 $\times$ 10$^{10}$ cm$^{-2}$ at the top GaN layer. However, the DD in the AlGaN/GaN MQW region is only 2.5 $\times$ 10$^{10}$ cm$^{-2}$. Figure 3(c) shows the plane-view bright-field TEM image from the top surface. The DD was estimated to be about 3.2

![Image](https://example.com/image.png)
peak energy at 3.62 eV can be clearly observed at 13 K. According to previous report, the emission peak energy of 3.62 eV could be attributed to the LO phonon. Additionally, the inset of Fig. 4 shows the CL image of the sample which has near uniform brightness with few dark spots. It was well known that the dark spots in CL image were related to nonradiative centers in the defects of epilayers. Therefore the CL image data again suggest our sample has relatively low DD and superior crystalline quality.

In summary, we have grown low dislocation and high crystalline quality AlGaN/GaN MQWs on sapphire substrate by using the ALD grown AlGaN barrier consisted of AlN/GaN SLs. The AFM data show smooth surface morphology with a small surface roughness RMS value of about 0.35 nm and no surface cracks. The TEM and HRXRD measurements show that the grown sample has sharp interfaces between SL layers and QWs with good periodicity. The sample has near uniform CL image intensity at room temperature and narrow PL emission peak. The sample has a low DD of about $3.3 \times 10^7$ cm$^{-2}$. These results indicate that the AlGaN/GaN MQWs grown by the ALD technique is a viable method for growth of a device-quality AlGaN/GaN MQWs structure for various optical devices.

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